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TITLE: Post etch cleaning composition and process for dual damascene system

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The addition of a small amount of hydroxylamine in the base solution increases the removal efficiency while keeping the solution compatible with copper.

Table 5 shows the results on sample 2, consisting of blanket SiLK film (organic low-k dielectric) with patterned silicon dioxide. The results show that these chemistries can effectively remove the organic resist without damaging the organic dielectric.

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1560	(multilayer or multilayered or multi-layered) same (structure or structures) same (deposit or deposited or depositing) same substrate	USPAT	2002/07/16 16:38
2	BRS	L2	269	1 same (remove or removing or removed)	USPAT	2002/07/16 16:42
3	BRS	L3	38	2 same resist	USPAT	2002/07/16 16:42